

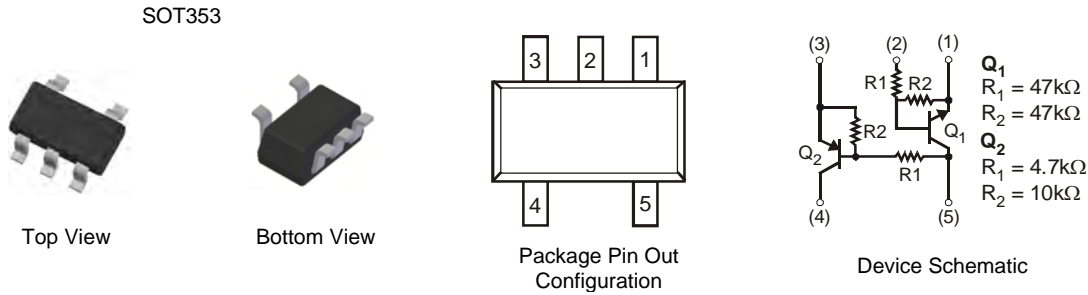
DUAL COMPLEMENTARY PRE-BIASED TRANSISTORS

Features

- Epitaxial Planar Die Construction
- Surface Mount Package Suited for Automated Assembly
- Simplifies Circuit Design and Reduces Board Space
- **Lead Free, RoHS Compliant (Note 1)**
- **Halogen and Antimony Free "Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT353
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed Over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)

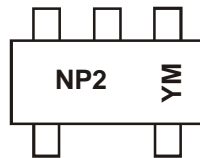


Ordering Information (Note 3)

| Part Number | Case | Packaging |
|-------------|--------|------------------|
| UMC5N-7 | SOT353 | 3000/Tape & Reel |

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



NP2 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: U = 2007)
 M = Month (ex: 9 = September)

Date Code Key

| Year | 2007 | 2008 | 2009 | 2010 | 2011 | 2012 | 2013 | 2014 | 2015 |
|------|------|------|------|------|------|------|------|------|------|
| Code | U | V | W | X | Y | Z | A | B | C |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |

Maximum Ratings, Pre-Biased NPN Transistor, Q₁ @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Value | Unit |
|-------------------|---------------------|------------|------|
| Supply Voltage | V _{CC} | 50 | V |
| Input Voltage | V _{IN} | -10 to +40 | V |
| Output Current | I _O | 30 | mA |
| Collector Current | I _{C(MAX)} | 100 | mA |

Maximum Ratings, Pre-Biased PNP Transistor, Q₂ @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Value | Unit |
|-------------------|---------------------|-----------|------|
| Supply Voltage | V _{CC} | -50 | V |
| Input Voltage | V _{IN} | -20 to +7 | V |
| Output Current | I _O | -100 | mA |
| Collector Current | I _{C(MAX)} | -100 | mA |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|--|-----------------------------------|-------------|------|
| Power Dissipation (Note 4) | P _D | 150 | mW |
| Thermal Resistance, Junction to Ambient Air (Note 4) | R _{θJA} | 833 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

Notes: 4. Device mounted on FR-4 PCB; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com>.

Electrical Characteristics, Pre-Biased NPN Transistor, Q₁ @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---------------------------------|--------------------------------|------|-----|------|------|--|
| Input Voltage | (Note 5) V _{I(OFF)} | 0.5 | — | — | V | V _{CC} = 5V, I _O = 100μA |
| | (Note 6) V _{I(ON)} | — | — | 3 | V | V _O = 0.3V, I _O = 2mA |
| Output Voltage | V _{O(ON)} | — | 0.1 | 0.3 | V | I _O /I _I = 10mA/0.5 mA |
| Input Current | I _I | — | — | 0.18 | mA | V _I = 5V |
| Output Current | I _{O(OFF)} | — | — | 0.5 | μA | V _{CC} = 50V, V _I = 0V |
| DC Current Gain | G _I | 68 | — | — | — | V _O = 5V, I _O = 5mA |
| Gain-Bandwidth Product (Note 7) | f _T | — | 250 | — | MHz | V _{CE} = 10V, I _E = -5mA, f = 100MHz |
| Input Resistance | R ₁ | 32.9 | 47 | 61.1 | kΩ | — |
| Resistance Ratio | R ₂ /R ₁ | 0.8 | 1 | 1.2 | — | — |

Notes: 5. The device is guaranteed to be in "OFF" state with V_{I(OFF)} up to 0.5V
 6. The device is guaranteed to be in "ON" state with V_{I(ON)} starting from 3V
 7. Characteristic of Transistor – for reference only.

Electrical Characteristics, Pre-Biased PNP Transistor, Q₂ @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---------------------------------|--------------------------------|------|------|------|------|--|
| Input Voltage | V _{I(OFF)} | -0.3 | — | — | V | V _{CC} = -5V, I _O = -100μA |
| | V _{I(ON)} | — | — | -2.5 | V | V _O = -0.3V, I _O = -20mA |
| Output Voltage | V _{O(ON)} | — | -0.1 | -0.3 | V | I _O /I _I = -10mA/-0.5 mA |
| Input Current | I _I | — | — | -1.8 | mA | V _I = -5V |
| Output Current | I _{O(OFF)} | — | — | -0.5 | μA | V _{CC} = -50V, V _I = 0V |
| DC Current Gain | G _I | 30 | — | — | — | V _O = -5V, I _O = -10mA |
| Gain-Bandwidth Product (Note 7) | f _T | — | 250 | — | MHz | V _{CE} = -10V, I _E = 5mA, f = 100MHz |
| Input Resistance | R ₁ | 3.29 | 4.7 | 6.11 | kΩ | — |
| Resistance Ratio | R ₂ /R ₁ | 1.7 | 2.1 | 2.6 | — | — |

Notes: 8. The device is guaranteed to be in "OFF" state with V_{I(OFF)} up to -0.3V
 9. The device is guaranteed to be in "ON" state with V_{I(ON)} starting from -2.5V
 10. Characteristic of Transistor – for reference only.

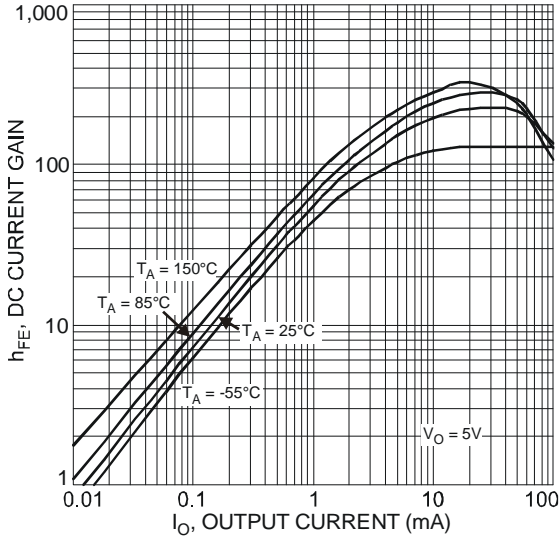


Fig. 1 Typical DC Current Gain vs. Output Current (Q1, NPN)

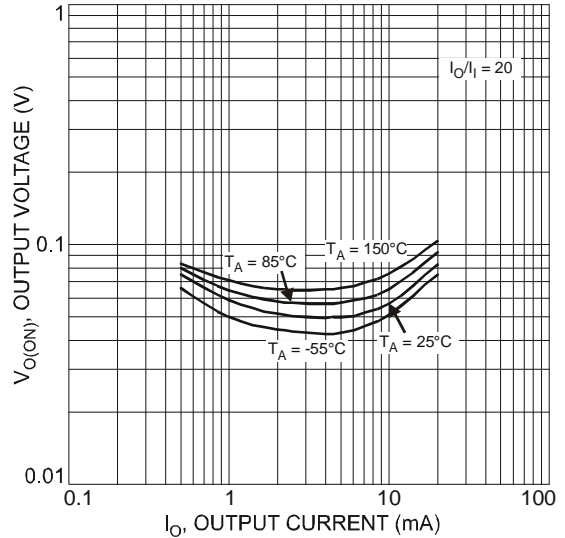


Fig. 2 Typical Output Voltage vs. Output Current (Q1, NPN)

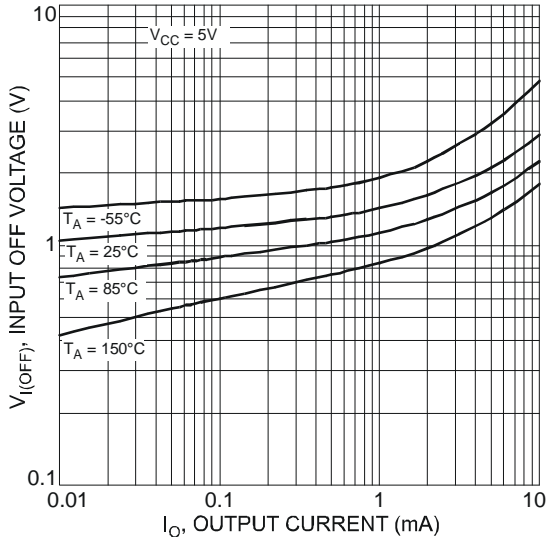


Fig. 3 Typical Input OFF Voltage vs. Output Current (Q1, NPN)

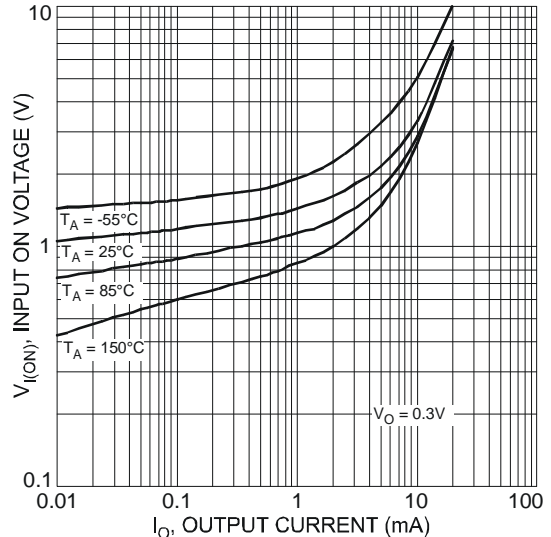


Fig. 4 Typical Input ON Voltage vs. Output Current (Q1, NPN)

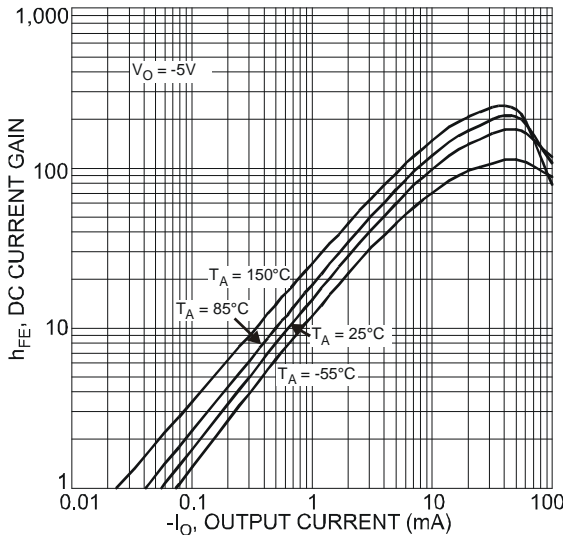


Fig. 5 Typical DC Current Gain vs. Output Current (Q2, PNP)

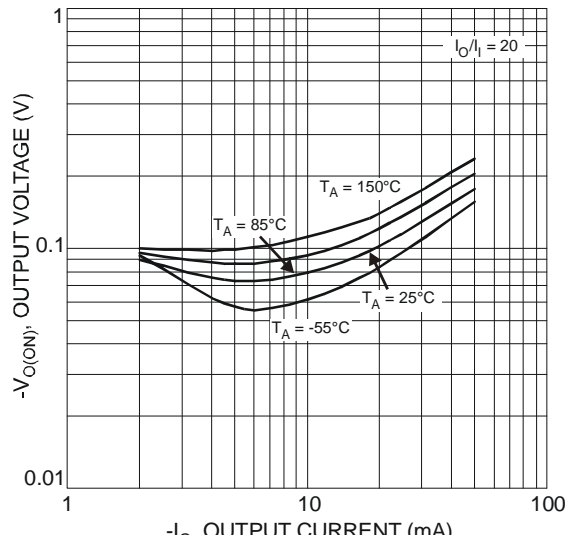


Fig. 6 Typical Output Voltage vs. Output Current (Q2, PNP)

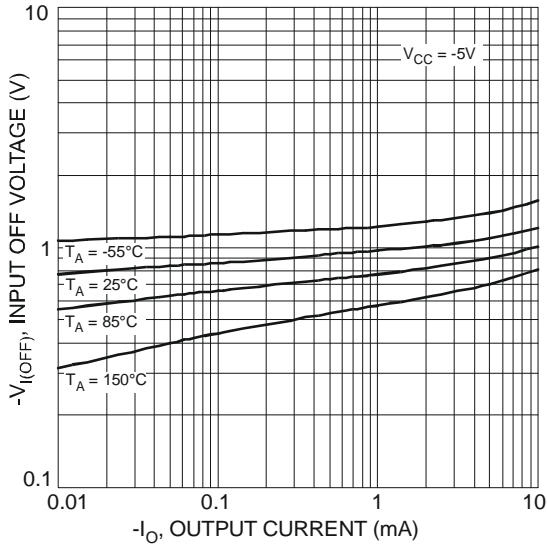


Fig. 7 Typical Input Off Voltage vs. Output Current (Q2, PNP)

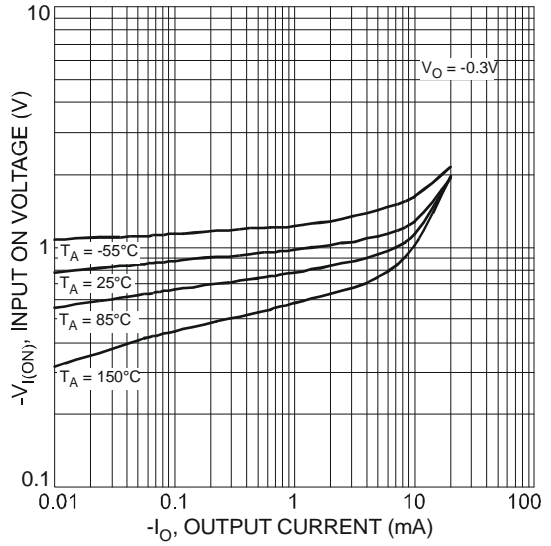
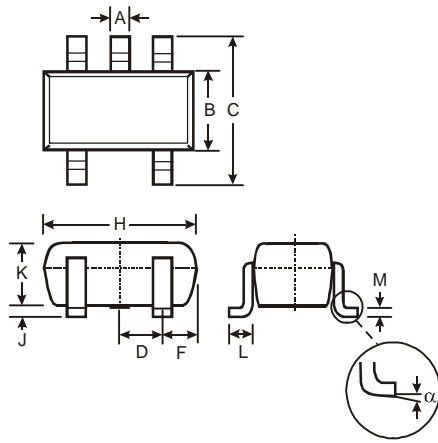


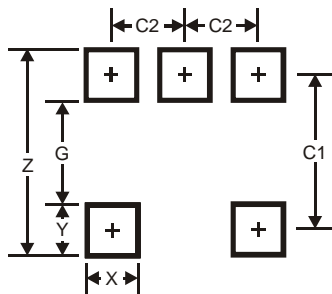
Fig. 8 Typical Input ON Voltage vs. Output Current (Q2, PNP)

Package Outline Dimensions



| SOT353 | | |
|----------------------|----------|------|
| Dim | Min | Max |
| A | 0.10 | 0.30 |
| B | 1.15 | 1.35 |
| C | 2.00 | 2.20 |
| D | 0.65 Typ | |
| F | 0.40 | 0.45 |
| H | 1.80 | 2.20 |
| J | 0 | 0.10 |
| K | 0.90 | 1.00 |
| L | 0.25 | 0.40 |
| M | 0.10 | 0.22 |
| α | 0° | 8° |
| All Dimensions in mm | | |

Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 2.5 |
| G | 1.3 |
| X | 0.42 |
| Y | 0.6 |
| C1 | 1.9 |
| C2 | 0.65 |

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